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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, Motor Control PWM, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	51
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f103ret6

List of figures

2.1 Device overview

The STM32F103xC/D/E high-density performance line family offers devices in six different package types: from 64 pins to 144 pins. Depending on the device chosen, different sets of peripherals are included, the description below gives an overview of the complete range of peripherals proposed in this family.

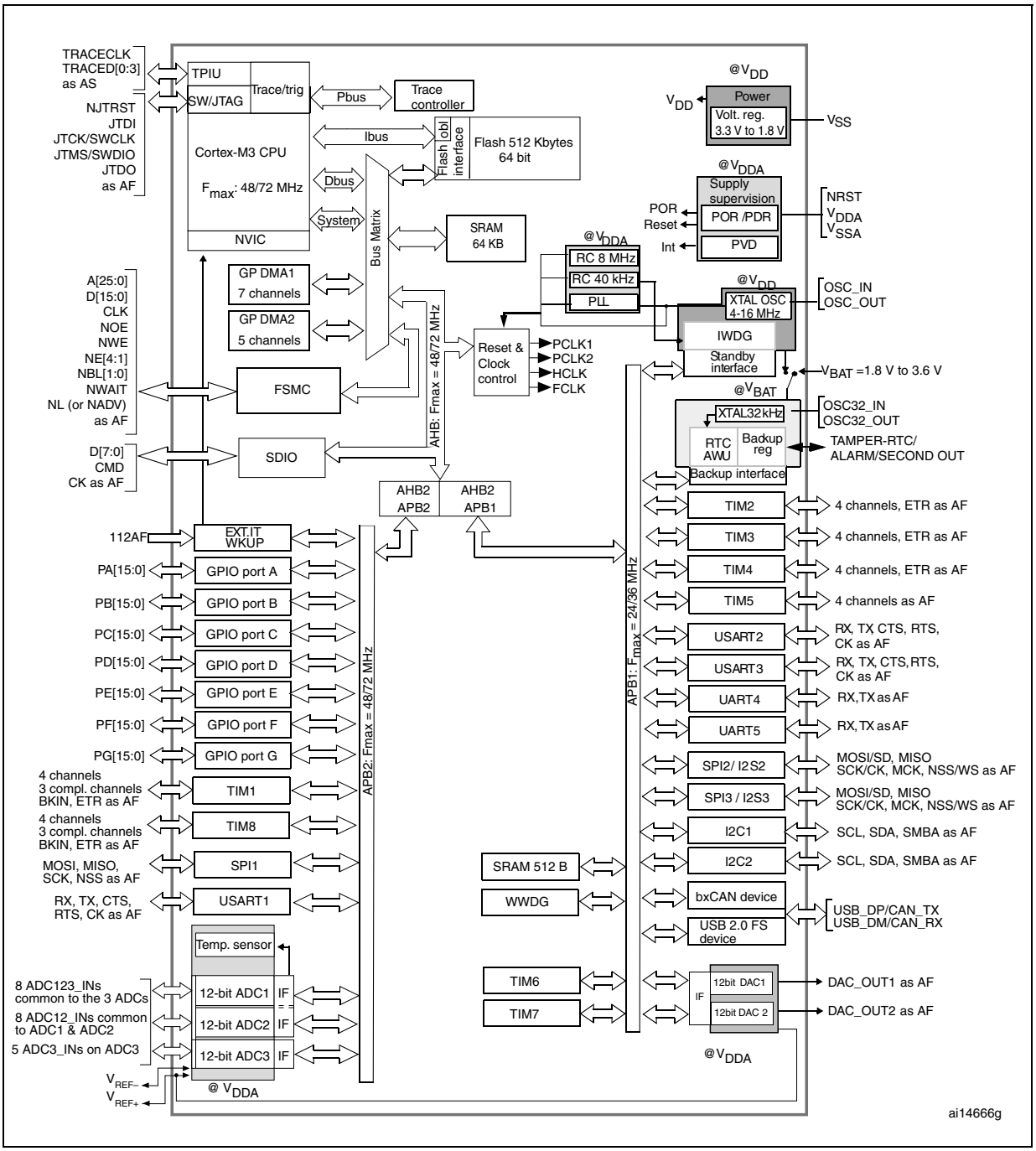
Figure 1 shows the general block diagram of the device family.

Table 2. STM32F103xC, STM32F103xD and STM32F103xE features and peripheral counts

Peripherals		STM32F103Rx			STM32F103Vx			STM32F103Zx		
Flash memory in Kbytes		256	384	512	256	384	512	256	384	512
SRAM in Kbytes		48	64(1)		48	64		48	64	
FSMC		No			Yes(2)			Yes		
Timers	General-purpose	4								
	Advanced-control	2								
	Basic	2								
Comm	SPI(I^2S)(3)	3(2)								
	I^2C	2								
	USART	5								
	USB	1								
	CAN	1								
	SDIO	1								
GPIOs		51			80			112		
12-bit ADC Number of channels		3 16			3 16			3 21		
12-bit DAC Number of channels		2 2								
CPU frequency		72 MHz								
Operating voltage		2.0 to 3.6 V								
Operating temperatures		Ambient temperatures: –40 to +85 °C /–40 to +105 °C (see *Table 10*) Junction temperature: –40 to + 125 °C (see *Table 10*)								
Package		LQFP64, WLCSP64			LQFP100, BGA100			LQFP144, BGA144		

1. 64 KB RAM for 256 KB Flash are available on devices delivered in CSP packages only.
2. For the LQFP100 and BGA100 packages, only FSMC Bank1 and Bank2 are available. Bank1 can only support a multiplexed NOR/PSRAM memory using the NE1 Chip Select. Bank2 can only support a 16- or 8-bit NAND Flash memory using the NCE2 Chip Select. The interrupt line cannot be used since Port G is not available in this package.
3. The SPI2 and SPI3 interfaces give the flexibility to work in an exclusive way in either the SPI mode or the I^2S audio mode.

Figure 1. STM32F103xC, STM32F103xD and STM32F103xE performance line block diagram



1. T_A = –40 °C to +85 °C (suffix 6, see *Table 75*) or –40 °C to +105 °C (suffix 7, see *Table 75*), junction temperature up to 105 °C or 125 °C, respectively.
2. AF = alternate function on I/O port pin.9

2.2 Full compatibility throughout the family

The STM32F103xC/D/E is a complete family whose members are fully pin-to-pin, software and feature compatible. In the reference manual, the STM32F103x4 and STM32F103x6 are identified as low-density devices, the STM32F103x8 and STM32F103xB are referred to as medium-density devices and the STM32F103xC, STM32F103xD and STM32F103xE are referred to as high-density devices.

Low-density and high-density devices are an extension of the STM32F103x8/B medium-density devices, they are specified in the STM32F103x4/6 and STM32F103xC/D/E datasheets, respectively. Low-density devices feature lower Flash memory and RAM capacities, less timers and peripherals. High-density devices have higher Flash memory and RAM capacities, and additional peripherals like SDIO, FSMC, I^2S and DAC while remaining fully compatible with the other members of the family.

The STM32F103x4, STM32F103x6, STM32F103xC, STM32F103xD and STM32F103xE are a drop-in replacement for the STM32F103x8/B devices, allowing the user to try different memory densities and providing a greater degree of freedom during the development cycle.

Moreover, the STM32F103xx performance line family is fully compatible with all existing STM32F101xx access line and STM32F102xx USB access line devices.

Table 3. STM32F103xx family

<table>
<tr><th rowspan="3">Pinout</th><th colspan="2">Low-density devices</th><th colspan="2">Medium-density devices</th><th colspan="3">High-density devices</th></tr>
<tr><th>16 KB Flash</th><th>32 KB Flash(1)</th><th>64 KB Flash</th><th>128 KB Flash</th><th>256 KB Flash</th><th>384 KB Flash</th><th>512 KB Flash</th></tr>
<tr><th>6 KB RAM</th><th>10 KB RAM</th><th>20 KB RAM</th><th>20 KB RAM</th><th>48 RAM</th><th>64 KB RAM</th><th>64 KB RAM</th></tr>
<tr><td>144</td><td colspan="2" rowspan="2"></td><td colspan="2" rowspan="2">3 × USARTs
3 × 16-bit timers
2 × SPIs, 2 × I2Cs, USB, CAN, 1 × PWM timer
2 × ADCs</td><td colspan="3" rowspan="2">5 × USARTs
4 × 16-bit timers, 2 × basic timers
3 × SPIs, 2 × I2Ss, 2 × I2Cs
USB, CAN, 2 × PWM timers
3 × ADCs, 2 × DACs, 1 × SDIO
FSMC (100- and 144-pin packages(2))</td></tr>
<tr><td>100</td></tr>
<tr><td>64</td><td colspan="2" rowspan="3">2 × USARTs
2 × 16-bit timers
1 × SPI, 1 × I2C, USB, CAN, 1 × PWM timer
2 × ADCs</td><td colspan="2" rowspan="2"></td><td colspan="3" rowspan="2"></td></tr>
<tr><td>48</td></tr>
<tr><td>36</td><td colspan="2"></td><td colspan="3"></td></tr>
</table>

1. For orderable part numbers that do not show the A internal code after the temperature range code (6 or 7), the reference datasheet for electrical characteristics is that of the STM32F103x8/B medium-density devices.
2. Ports F and G are not available in devices delivered in 100-pin packages.

2.3 Overview

2.3.1 ARM® Cortex®-M3 core with embedded Flash and SRAM

The ARM Cortex®-M3 processor is the latest generation of ARM processors for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced system response to interrupts.

The ARM Cortex®-M3 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices.

With its embedded ARM core, STM32F103xC, STM32F103xD and STM32F103xE performance line family is compatible with all ARM tools and software.

Figure 1 shows the general block diagram of the device family.

2.3.2 Embedded Flash memory

Up to 512 Kbytes of embedded Flash is available for storing programs and data.

2.3.3 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

2.3.4 Embedded SRAM

Up to 64 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states.

2.3.5 FSMC (flexible static memory controller)

The FSMC is embedded in the STM32F103xC, STM32F103xD and STM32F103xE performance line family. It has four Chip Select outputs supporting the following modes: PC Card/Compact Flash, SRAM, PSRAM, NOR and NAND.

Functionality overview:

- The three FSMC interrupt lines are ORed in order to be connected to the NVIC
- Write FIFO
- Code execution from external memory except for NAND Flash and PC Card
- The targeted frequency, f_{CLK}, is HCLK/2, so external access is at 36 MHz when HCLK is at 72 MHz and external access is at 24 MHz when HCLK is at 48 MHz

2.3.28 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with temperature. The conversion range is between 2 V < V_{DDA} < 3.6 V. The temperature sensor is internally connected to the ADC1_IN16 input channel which is used to convert the sensor output voltage into a digital value.

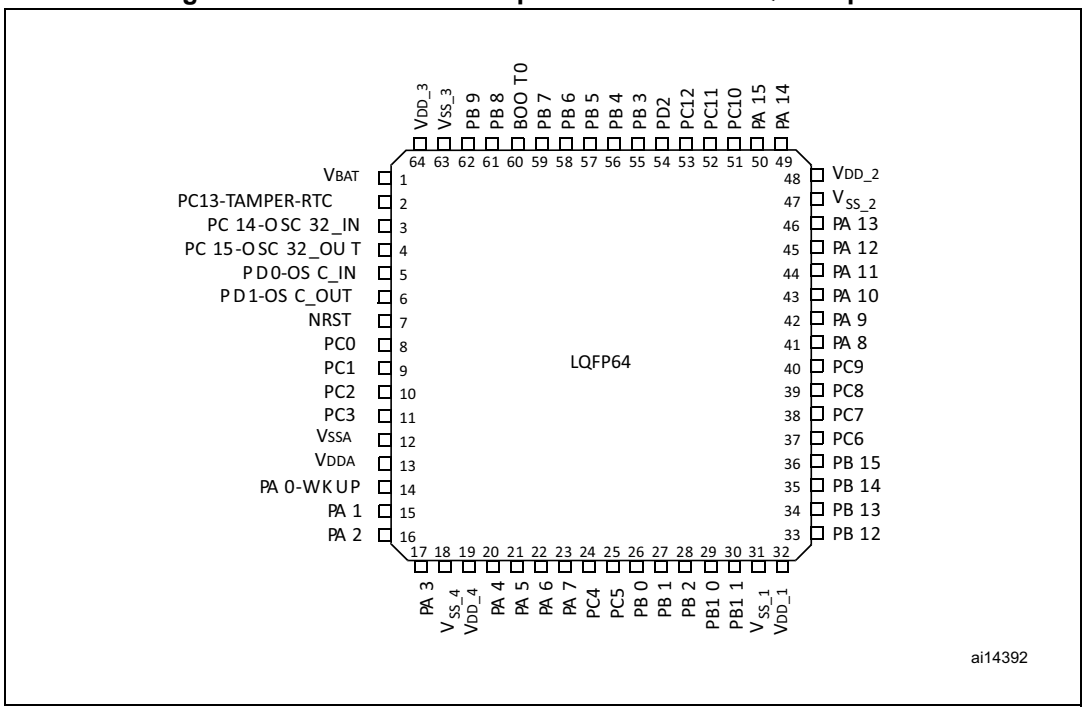
2.3.29 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP Interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target. The JTAG TMS and TCK pins are shared respectively with SWDIO and SWCLK and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

2.3.30 Embedded Trace Macrocell™

The ARM® Embedded Trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32F10xxx through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. The TPA is connected to a host computer using USB, Ethernet, or any other high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer running debugger software. TPA hardware is commercially available from common development tool vendors. It operates with third party debugger software tools.

Figure 7. STM32F103xC/D/E performance line LQFP64 pinout

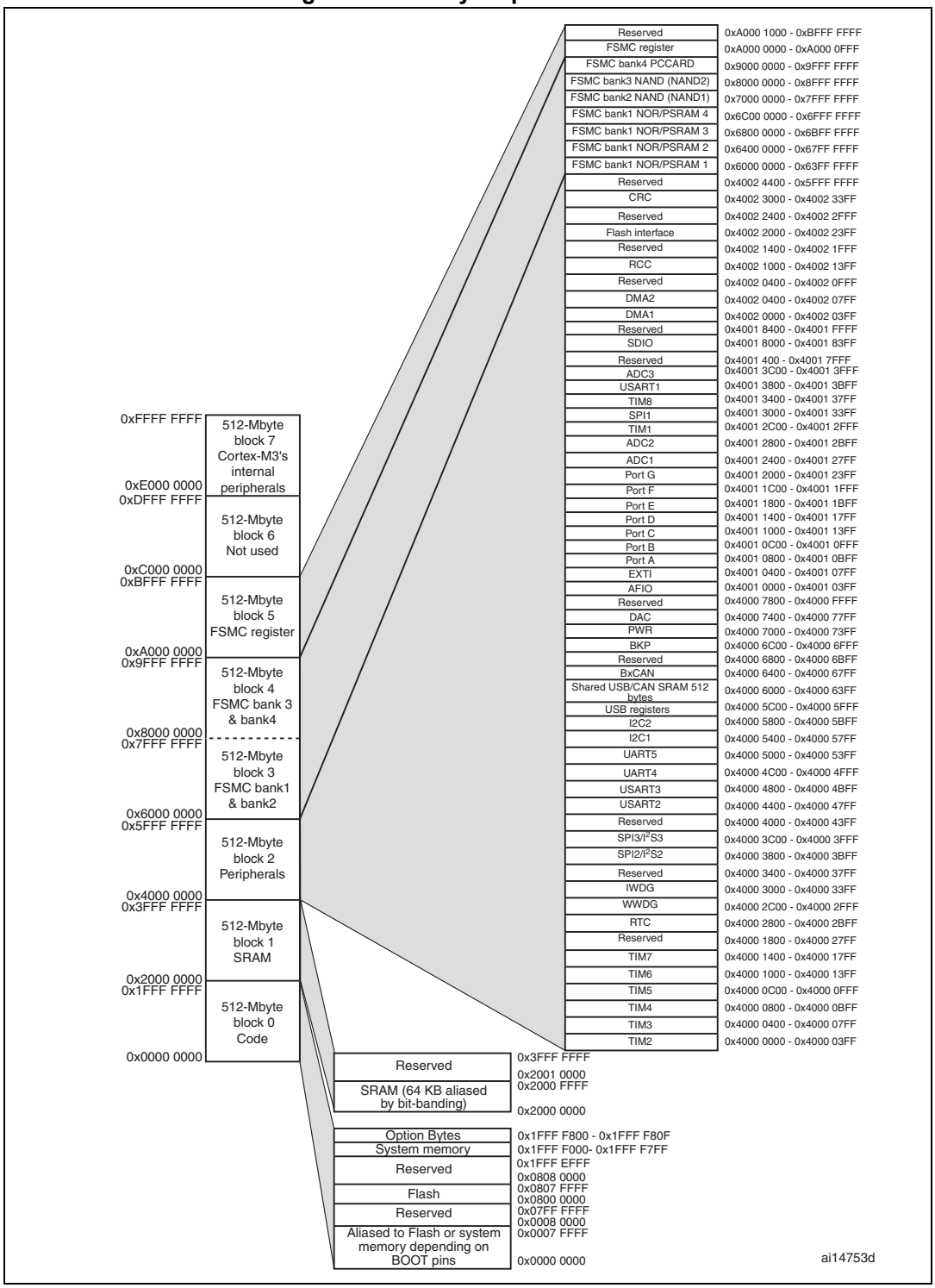


1. The above figure shows the package top view.

4 Memory mapping

The memory map is shown in *Figure 9*.

Figure 9. Memory map



5.3.4 Embedded reference voltage

The parameters given in *Table 13* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 10*.

Table 13. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	–40 °C < T_A < +105 °C	1.16	1.20	1.26	V
		–40 °C < T_A < +85 °C	1.16	1.20	1.24	
$T_{S\_vrefint}$(1)	ADC sampling time when reading the internal reference voltage	-	-	5.1	17.1(2)	µs
V_{RERINT}(2)	Internal reference voltage spread over the temperature range	V_{DD} = 3 V ±10 mV	-	-	10	mV
T_{Coeff}(2)	Temperature coefficient	-	-	-	100	ppm/°C

1. Shortest sampling time can be determined in the application by multiple iterations.
2. Guaranteed by design.

5.3.5 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.
The current consumption is measured as described in *Figure 13: Current consumption measurement scheme*.
All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to Dhrystone 2.1 code.

Maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time is adjusted to the f_{HCLK} frequency (0 wait state from 0 to 24 MHz, 1 wait state from 24 to 48 MHz and 2 wait states above)
- Prefetch in ON (reminder: this bit must be set before clock setting and bus prescaling)
- When the peripherals are enabled $f_{PCLK1} = f_{HCLK}/2$, $f_{PCLK2} = f_{HCLK}$

The parameters given in *Table 14*, *Table 15* and *Table 16* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 10*.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 24*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 24. LSE oscillator characteristics (f_{LSE} = 32.768 kHz)(1)(2)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R_F	Feedback resistor	-		-	5	-	MΩ
C(2)	Recommended load capacitance versus equivalent serial resistance of the crystal (R_S)	R_S = 30 kΩ		-	-	15	pF
I_2	LSE driving current	V_{DD} = 3.3 V, V_{IN} = V_{SS}		-	-	1.4	µA
g_m	Oscillator transconductance	-		5	-	-	µA/V
$t_{SU(LSE)}$(3)	Startup time	V_{DD} is stabilized	T_A = 50 °C	-	1.5	-	s
			T_A = 25 °C	-	2.5	-	
			T_A = 10 °C	-	4	-	
			T_A = 0 °C	-	6	-	
			T_A = -10 °C	-	10	-	
			T_A = -20 °C	-	17	-	
			T_A = -30 °C	-	32	-	
			T_A = -40 °C	-	60	-	

1. Guaranteed by characterization results.
2. Refer to the note and caution paragraphs below the table, and to the application note AN2867 “Oscillator design guide for ST microcontrollers”.
3. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) until a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer, PCB layout and humidity.

Note: For C_{L1} and C_{L2}, it is recommended to use high-quality ceramic capacitors in the 5 pF to 15 pF range selected to match the requirements of the crystal or resonator (see Figure 23). C_{L1} and C_{L2}, are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}.
Load capacitance C_L has the following formula: $C_L = C_{L1} \times C_{L2} / (C_{L1} + C_{L2}) + C_{stray}$ where C_{stray} is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.

Caution: To avoid exceeding the maximum value of C_{L1} and C_{L2} (15 pF) it is strongly recommended to use a resonator with a load capacitance $C_L \leq 7$ pF. Never use a resonator with a load capacitance of 12.5 pF.
Example: if you choose a resonator with a load capacitance of C_L = 6 pF, and C_{stray} = 2 pF, then C_{L1} = C_{L2} = 8 pF.

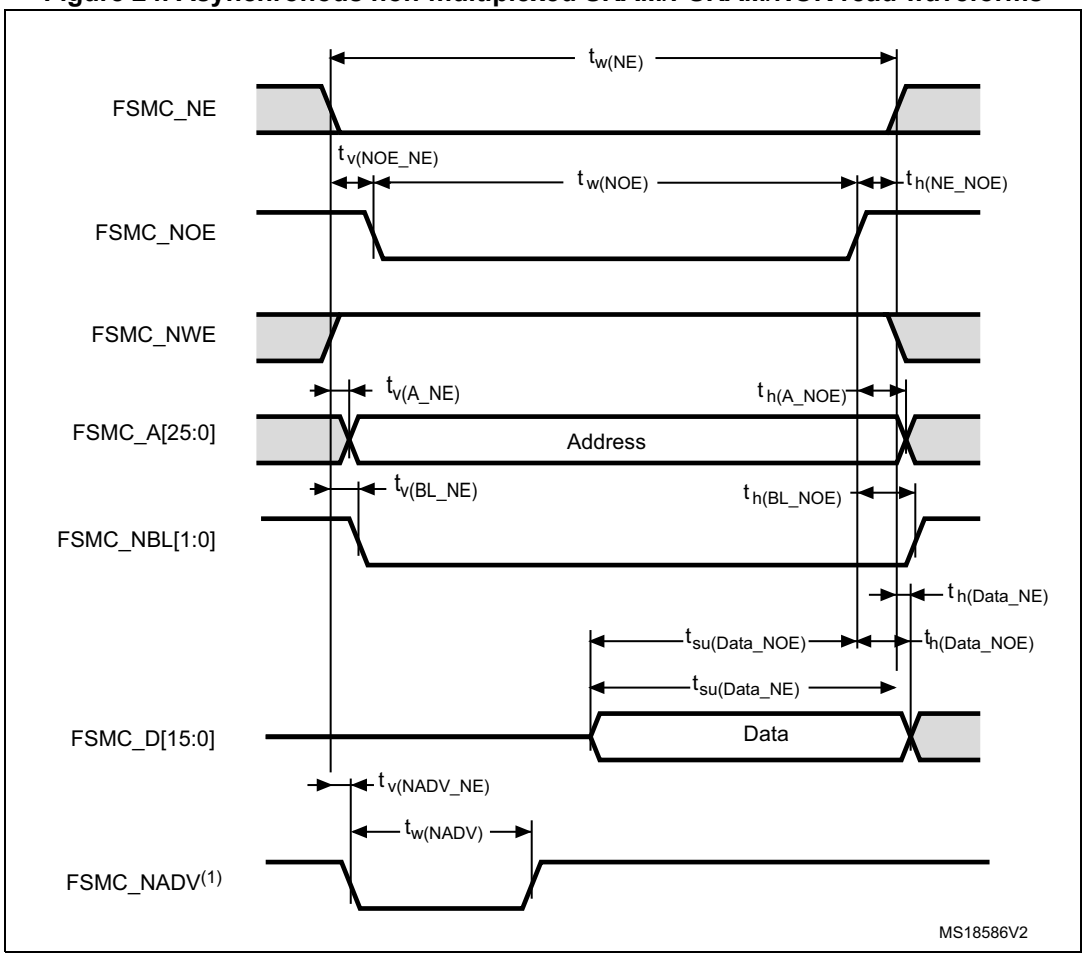
5.3.10 FSMC characteristics

Asynchronous waveforms and timings

Figure 24 through *Figure 27* represent asynchronous waveforms and *Table 31* through *Table 34* provide the corresponding timings. The results shown in these tables are obtained with the following FSMC configuration:

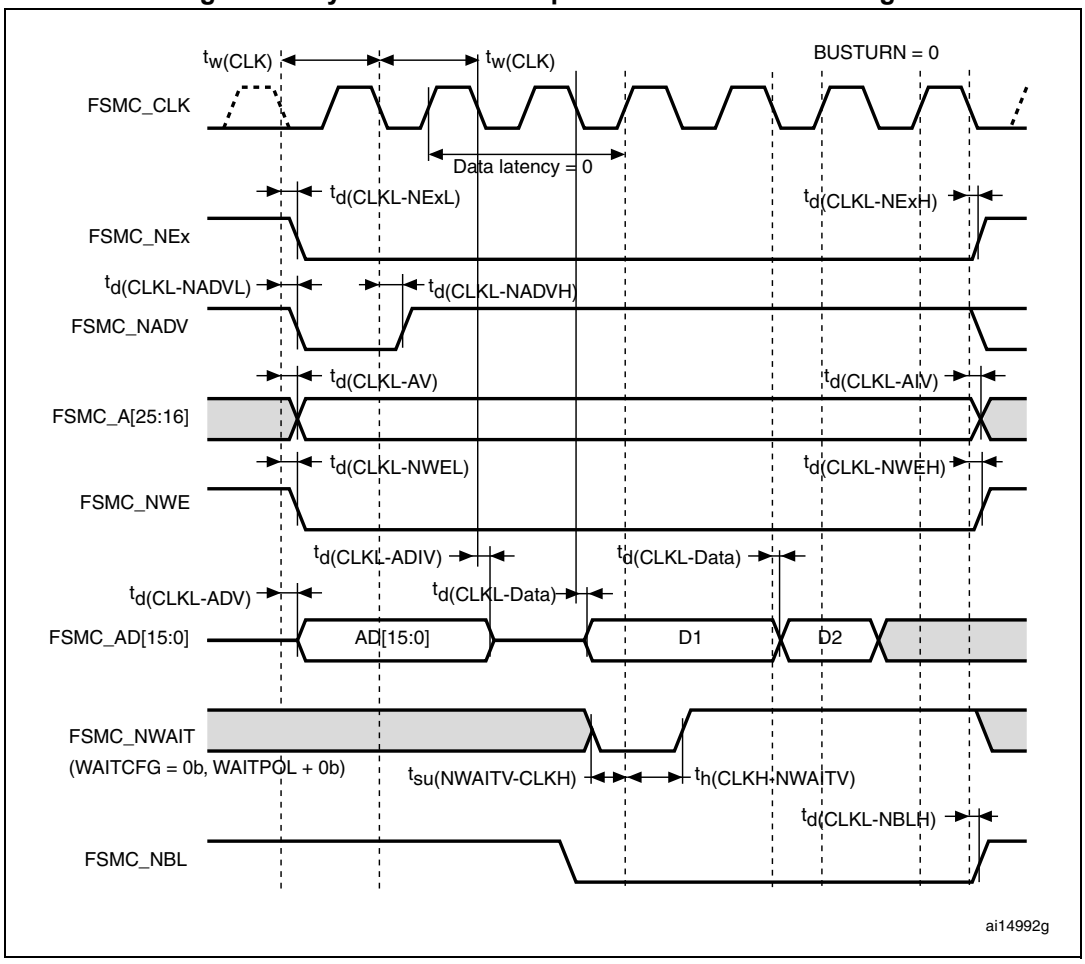
- AddressSetupTime = 0
- AddressHoldTime = 1
- DataSetupTime = 1

Figure 24. Asynchronous non-multiplexed SRAM/PSRAM/NOR read waveforms



1. Mode 2/B, C and D only. In Mode 1, FSMC_NADV is not used.

Figure 29. Synchronous multiplexed PSRAM write timings

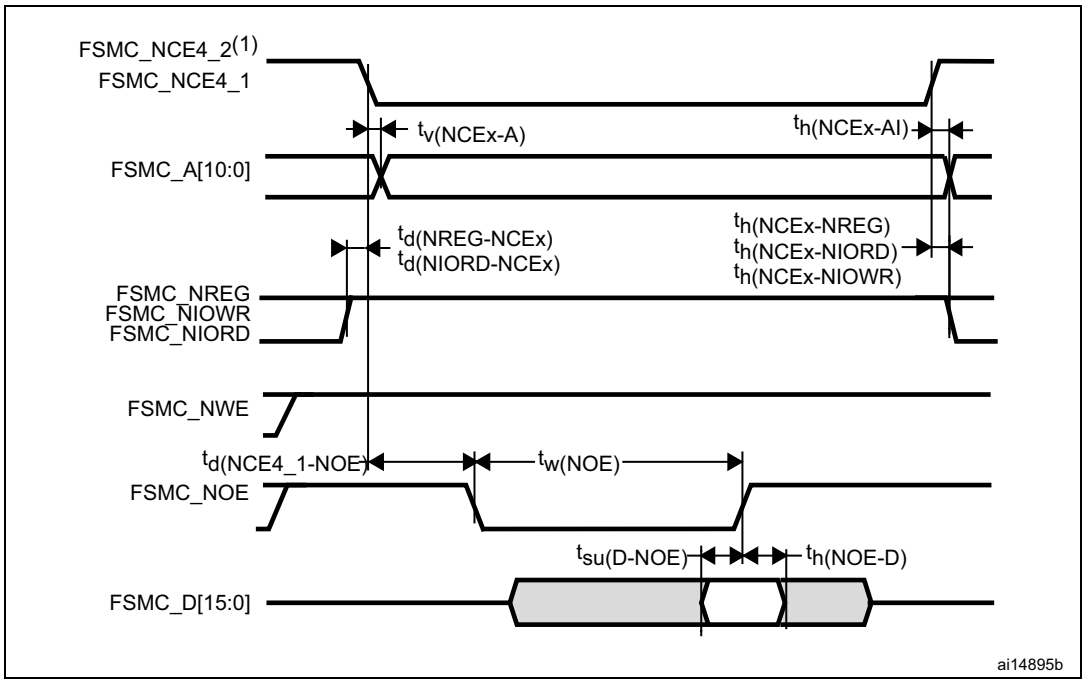


PC Card/CompactFlash controller waveforms and timings

Figure 32 through *Figure 37* represent synchronous waveforms and *Table 39* provides the corresponding timings. The results shown in this table are obtained with the following FSMC configuration:

- COM.FSMC_SetupTime = 0x04;
- COM.FSMC_WaitSetupTime = 0x07;
- COM.FSMC_HoldSetupTime = 0x04;
- COM.FSMC_HiZSetupTime = 0x00;
- ATT.FSMC_SetupTime = 0x04;
- ATT.FSMC_WaitSetupTime = 0x07;
- ATT.FSMC_HoldSetupTime = 0x04;
- ATT.FSMC_HiZSetupTime = 0x00;
- IO.FSMC_SetupTime = 0x04;
- IO.FSMC_WaitSetupTime = 0x07;
- IO.FSMC_HoldSetupTime = 0x04;
- IO.FSMC_HiZSetupTime = 0x00;
- TCLRSetupTime = 0;
- TARSetupTime = 0;

Figure 32. PC Card/CompactFlash controller waveforms for common memory read access



1. FSMC_NCE4_2 remains high (inactive during 8-bit access.

Figure 37. PC Card/CompactFlash controller waveforms for I/O space write access

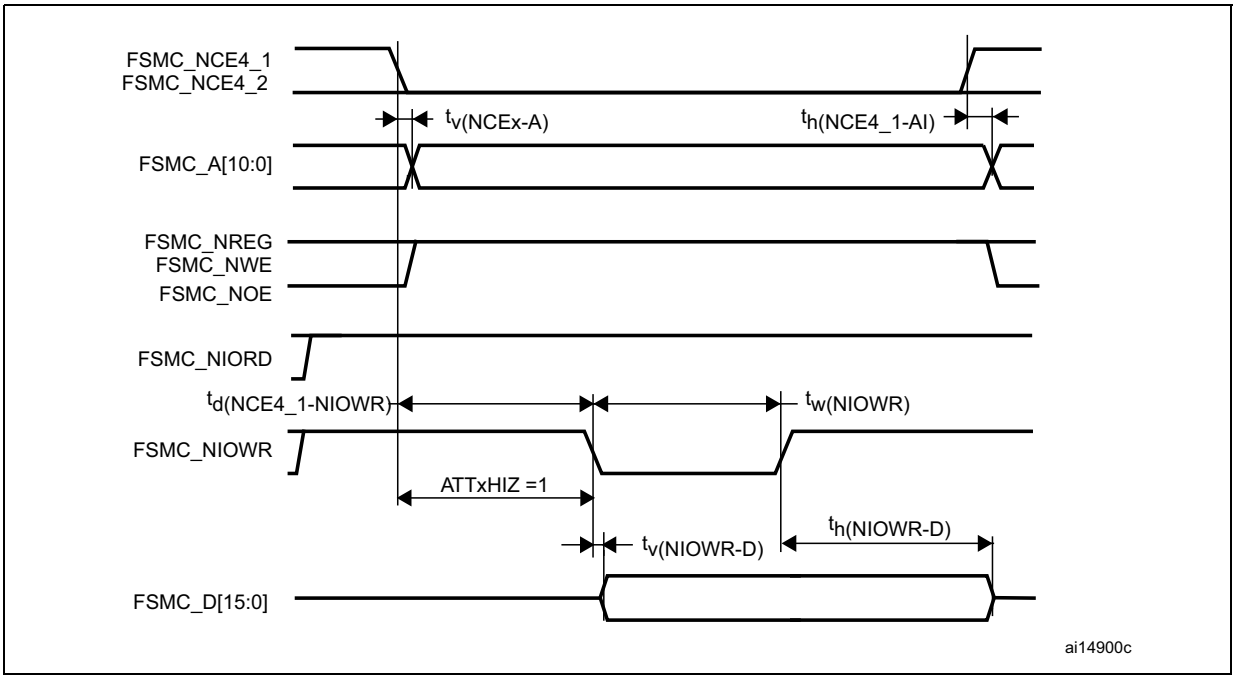


Table 39. Switching characteristics for PC Card/CF read and write cycles(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{v(NCEx-A)}$ $t_{v(NCE4\_1-A)}$	FSMC_NCEx low (x = 4_1/4_2) to FSMC_Ay valid (y = 0...10) FSMC_NCE4_1 low (x = 4_1/4_2) to FSMC_Ay valid (y = 0...10)	-	0	ns
$t_{h(NCEx-AI)}$ $t_{h(NCE4\_1-AI)}$	FSMC_NCEx high (x = 4_1/4_2) to FSMC_Ax invalid (x = 0...10) FSMC_NCE4_1 high (x = 4_1/4_2) to FSMC_Ax invalid (x = 0...10)	2.5	-	ns
$t_{d(NREG-NCEx)}$ $t_{d(NREG-NCE4\_1)}$	FSMC_NCEx low to FSMC_NREG valid FSMC_NCE4_1 low to FSMC_NREG valid	-	5	ns
$t_{h(NCEx-NREG)}$ $t_{h(NCE4\_1-NREG)}$	FSMC_NCEx high to FSMC_NREG invalid FSMC_NCE4_1 high to FSMC_NREG invalid	t_{HCLK} + 3	-	ns
$t_{d(NCE4\_1-NOE)}$	FSMC_NCE4_1 low to FSMC_NOE low	-	$5t_{HCLK}$ + 2	ns
$t_{w(NOE)}$	FSMC_NOE low width	$8t_{HCLK}$ –1.5	$8t_{HCLK}$ + 1	ns
$t_{d(NOE-NCE4\_1}$	FSMC_NOE high to FSMC_NCE4_1 high	$5t_{HCLK}$ + 2	-	ns
$t_{su(D-NOE)}$	FSMC_D[15:0] valid data before FSMC_NOE high	25	-	ns
$t_{h(NOE-D)}$	FSMC_D[15:0] valid data after FSMC_NOE high	15	-	ns
$t_{w(NWE)}$	FSMC_NWE low width	$8t_{HCLK}$ – 1	$8t_{HCLK}$ + 2	ns
$t_{d(NWE-NCE4\_1)}$	FSMC_NWE high to FSMC_NCE4_1 high	$5t_{HCLK}$ + 2	-	ns
$t_{d(NCE4\_1-NWE)}$	FSMC_NCE4_1 low to FSMC_NWE low	-	$5t_{HCLK}$ + 1.5	ns
$t_{v(NWE-D)}$	FSMC_NWE low to FSMC_D[15:0] valid	-	0	ns
$t_{h(NWE-D)}$	FSMC_NWE high to FSMC_D[15:0] invalid	$11t_{HCLK}$	-	ns
$t_{d(D-NWE)}$	FSMC_D[15:0] valid before FSMC_NWE high	$13t_{HCLK}$	-	ns

Figure 39. NAND controller waveforms for write access

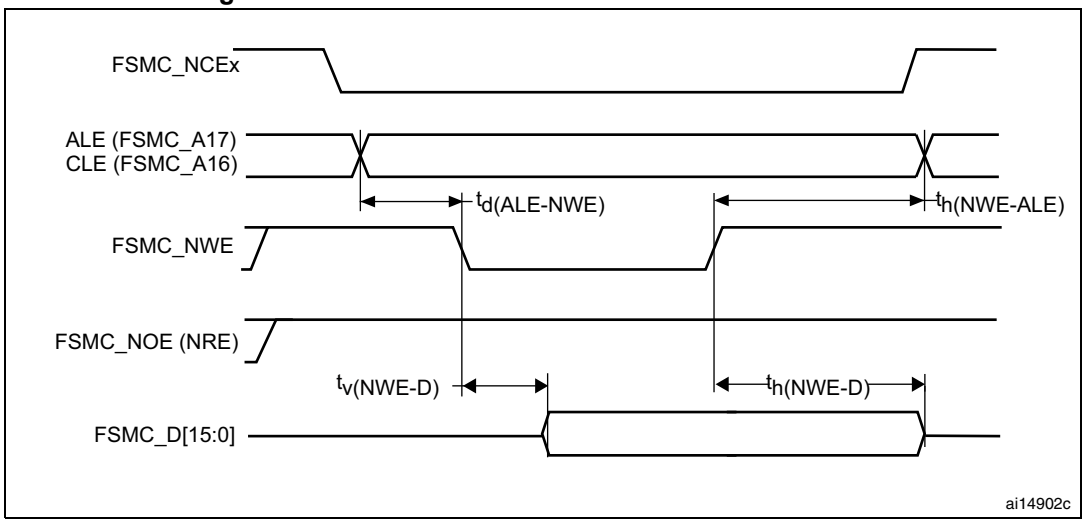


Figure 40. NAND controller waveforms for common memory read access

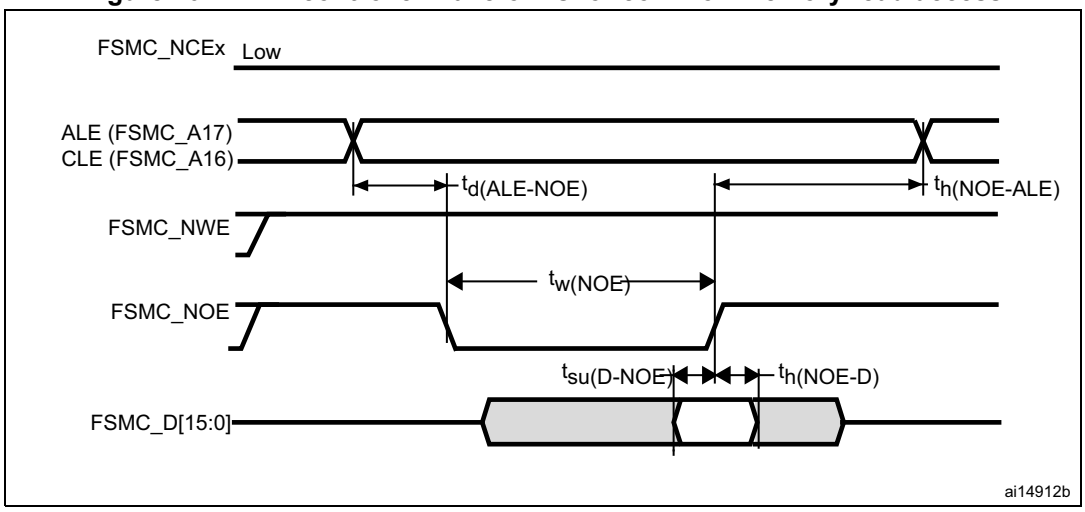


Table 44. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = +105 °C conforming to JESD78A	II level A

5.3.13 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibilty to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of spec current injection on adjacent pins or other functional failure (for example reset, oscillator frequency deviation).

The test results are given in *Table 45*

Table 45. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on OSC_IN32, OSC_OUT32, PA4, PA5, PC13	-0	+0	mA
	Injected current on all FT pins	-5	+0	
	Injected current on any other pin	-5	+5	

5.3.14 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 46* are derived from tests performed under the conditions summarized in *Table 10*. All I/Os are CMOS and TTL compliant.

Table 46. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Standard IO input low level voltage	-	–0.3	-	0.28*(V_{DD}-2 V)+0.8 V	V
	IO FT(1) input low level voltage		–0.3	-	0.32*(V_{DD}-2 V)+0.75 V	V
V_{IH}	Standard IO input high level voltage	-	0.41*(V_{DD}-2 V)+1.3 V	-	V_{DD}+0.3	V
	IO FT(1) input high level voltage	V_{DD} > 2 V	0.42*(V_{DD}-2 V)+1 V	-	5.5	V
		V_{DD} ≤2 V			5.2	
V_{hys}	Standard IO Schmitt trigger voltage hysteresis(2)	-	200	-	-	mV
	IO FT Schmitt trigger voltage hysteresis(2)		5% V_{DD}(3)	-	-	mV
I_{lkg}	Input leakage current (4)	V_{SS} ≤V_{IN} ≤V_{DD} Standard I/Os	-	-	±1	µA
		V_{IN}= 5 V, I/O FT	-	-	3	
R_{PU}	Weak pull-up equivalent resistor(5)	V_{IN} = V_{SS}	30	40	50	kΩ
R_{PD}	Weak pull-down equivalent resistor(5)	V_{IN} = V_{DD}	30	40	50	kΩ
C_{IO}	I/O pin capacitance	-	-	5	-	pF

1. FT = Five-volt tolerant. In order to sustain a voltage higher than V_{DD}+0.3 the internal pull-up/pull-down resistors must be disabled.
2. Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization results.
3. With a minimum of 100 mV.
4. Leakage could be higher than max. if negative current is injected on adjacent pins.
5. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This MOS/NMOS contribution to the series resistance is minimum (~10% order).

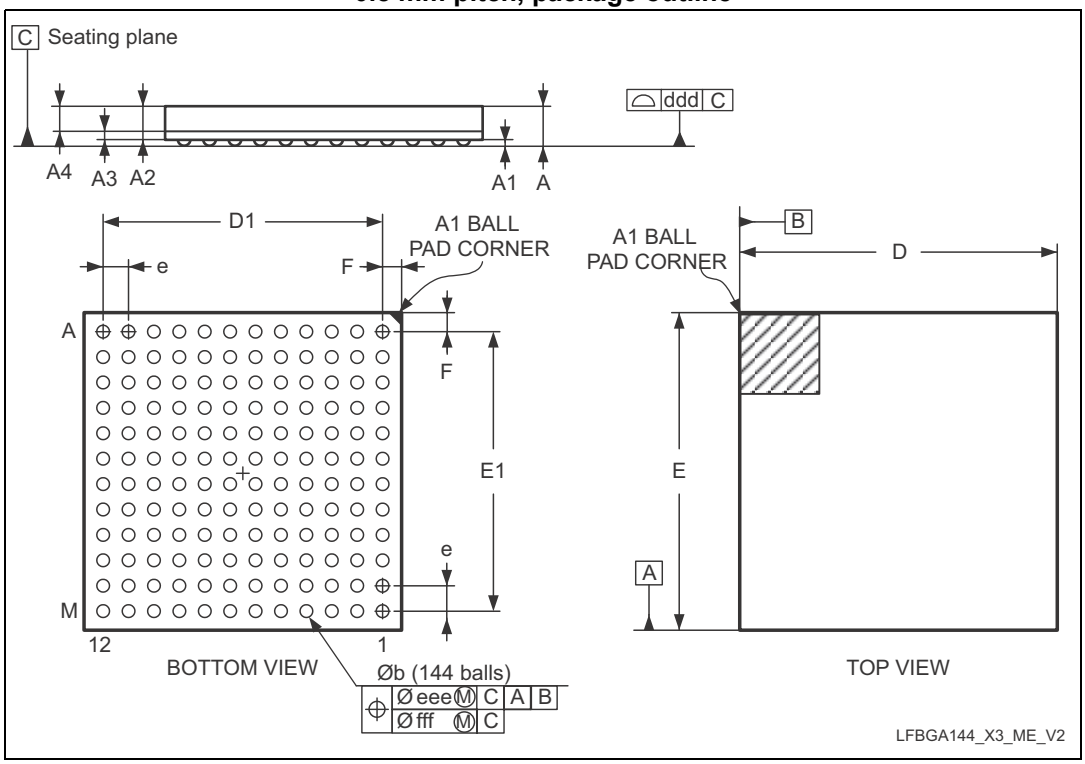
All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements is shown in *Figure 42* and *Figure 43* for standard I/Os, and in *Figure 44* and *Figure 45* for 5 V tolerant I/Os.

6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

6.1 LFBGA144 package information

Figure 62. LFBGA144 – 144-ball low profile fine pitch ball grid array, 10 x 10 mm, 0.8 mm pitch, package outline



1. Drawing is not to scale.

Table 65. LFBGA144 – 144-ball low profile fine pitch ball grid array, 10 x 10 mm, 0.8 mm pitch, package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Typ	Min	Max
A[2]	-	-	1.700	-	-	0.0669
A1	0.250	0.300	0.350	0.098	0.0118	0.0138
A2	0.810	0.910	1.010	0.0319	0.0358	0.0398
A3	0.225	0.26	0.295	0.0089	0.0102	0.0116
A4	0.585	0.650	0.715	0.0230	0.0256	0.0281

7 Part numbering

Table 75. Ordering information scheme

Example: STM32 F 103 R C T 6 xxx

Device family

STM32 = ARM-based 32-bit microcontroller

Product type

F = general-purpose

Device subfamily

103 = performance line

Pin count

R = 64 pins
V = 100 pins
Z = 144 pins

Flash memory size

C = 256 Kbytes of Flash memory
D = 384 Kbytes of Flash memory
E = 512 Kbytes of Flash memory

Package

H = BGA
T = LQFP
Y = WLCSP64

Temperature range

6 = Industrial temperature range, –40 to 85 °C.
7 = Industrial temperature range, –40 to 105 °C.

Options

xxx = programmed parts
TR = tape and real

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.